S-5470 Series

ULTRA-LOW CURRENT CONSUMPTION PHOTOCURRENT DETECTION IC

www.sii-ic.com

Rev.1.2_01

The S-5470 Series, developed by CMOS technology, is a photocurrent detection IC with an ultra-low current consumption. It detects 0.7 nA typ. photocurrent generated by an external photodiode (PD) or LED. It also has a function to detect the difference of photocurrent level between two external photodiodes (PDs) or LEDs.
Due to its ultra-low current consumption and low-voltage operation, the S-5470 Series is suitable for battery-operated small mobile device applications.

■ Features

- Ultra-low current consumption: $I_{DD} \leq 0.1$ nA typ.
- Micro-photocurrent detection: $I_{DET} = 0.7$ nA typ.
- Wide operation voltage range: $V_{DD} = 0.9$ V to 5.5 V
- Detection of certain photocurrent level: Detects certain level of photocurrent generated by external photodiode (PD) or LED
- Detection of photocurrent level difference: Detects the difference of photocurrent level between external photodiodes (PDs) or LEDs
- External parts: One or two external photodiodes (PDs) or LEDs*1
- Lead-free (Sn 100%), halogen-free*2

*1. The required number of PDs or LEDs changes with operation.
Regarding selection of PD and LED, refer to "**3. Selection of PD or LED**" in "**■ Application Circuits**".
*2. Refer to "**■ Product Name Structure**" for details.

■ Applications

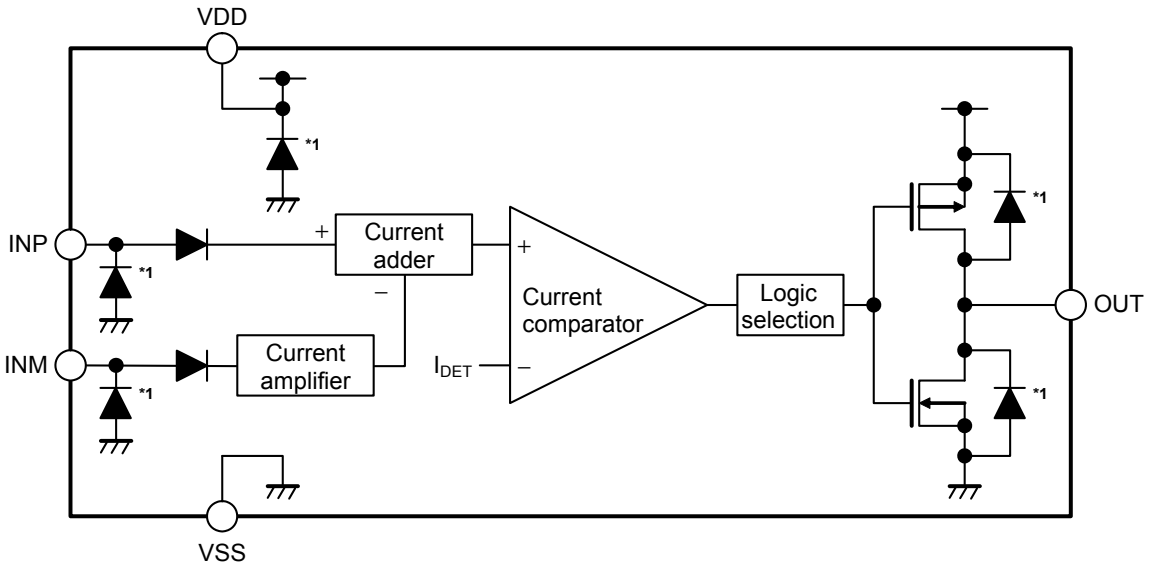
- Shading detection
- Light and darkness detection
- Non-contact switch for portable and wireless device

■ Package

- SOT-23-5

■ Block Diagrams

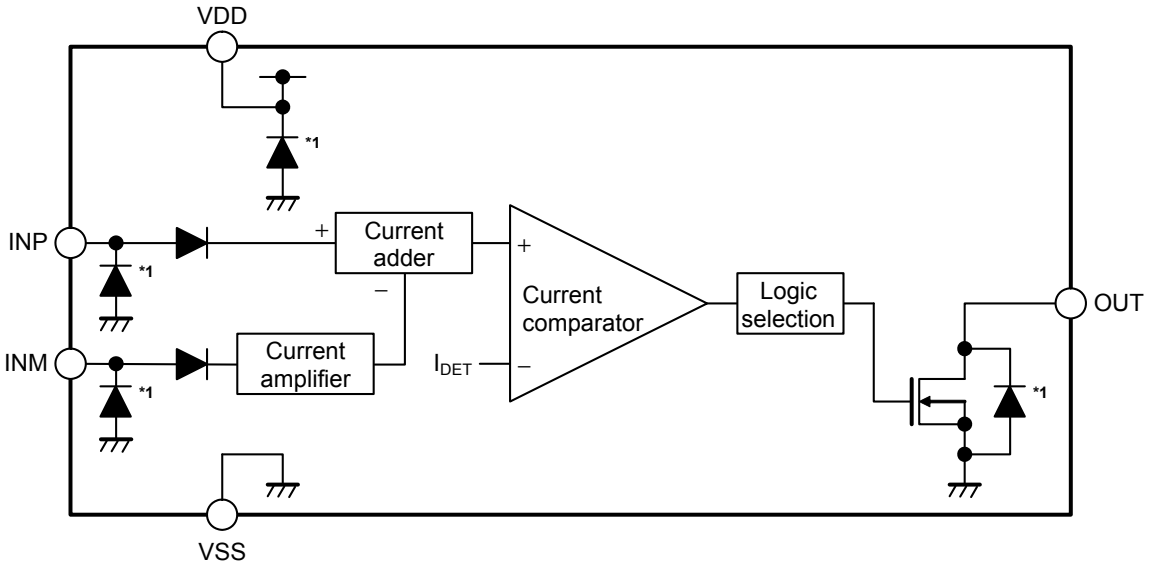
1. CMOS output product



***1.** Parasitic diode

Figure 1

2. Nch open-drain output product



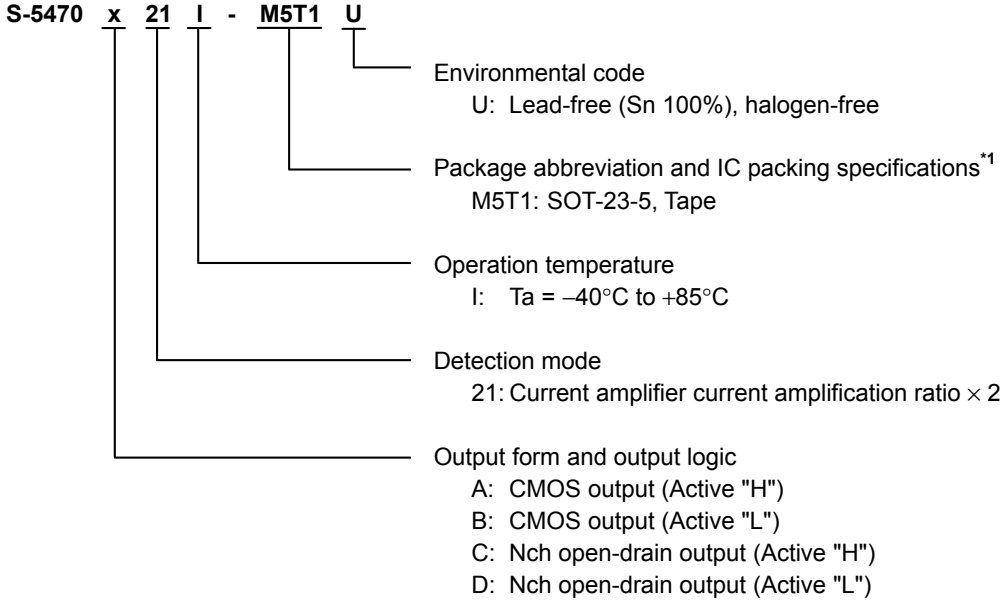
***1.** Parasitic diode

Figure 2

■ Product Name Structure

Users can select the output form and output logic for the S-5470 Series. Refer to "**1. Product name**" regarding the contents of the product name, "**2. Package**" regarding the package drawings, "**3. Product name list**" regarding details of the product name.

1. Product name



***1.** Refer to the tape drawing.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
SOT-23-5	MP005-A-P-SD	MP005-A-C-SD	MP005-A-R-SD

3. Product name list

Table 2

Product Name	Output Form	Output Logic	Detection Mode
S-5470A21I-M5T1U	CMOS output	Active "H"	Current amplifier current amplification ratio × 2
S-5470B21I-M5T1U	CMOS output	Active "L"	Current amplifier current amplification ratio × 2
S-5470C21I-M5T1U	Nch open-drain output	Active "H"	Current amplifier current amplification ratio × 2
S-5470D21I-M5T1U	Nch open-drain output	Active "L"	Current amplifier current amplification ratio × 2

Remark Please contact our sales office for products other than the above.

■ Pin Configuration

1. SOT-23-5

Top view

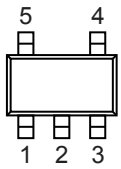


Figure 3

Table 3

Pin No.	Symbol	Description
1	VDD	Power supply pin
2	VSS	GND pin
3	INM	Reference current input pin
4	INP	Detection current input pin
5	OUT	Output pin

■ Absolute Maximum Ratings

Table 4

(Ta = +25°C unless otherwise specified)

Item		Symbol	Absolute Maximum Rating	Unit
Power supply voltage		V_{DD}	V_{SS} – 0.3 to V_{SS} + 7.0	V
Input voltage		V_{INP}, V_{INM}	V_{SS} – 0.3 to V_{SS} + 7.0	V
Output voltage	CMOS output product	V_{OUT}	V_{SS} – 0.3 to V_{DD} + 0.3	V
	Nch open-drain output product		V_{SS} – 0.3 to V_{SS} + 7.0	V
Output pin current		I_{SOURCE}	20	mA
		I_{SINK}	20	mA
Power dissipation		P_D	600*1	mW
Operation ambient temperature		T_{opr}	−40 to +85	°C
Storage temperature		T_{stg}	−55 to +125	°C

***1.** When mounted on board
[Mounted board]
(1) Board size: 114.3 mm × 76.2 mm × t1.6 mm
(2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

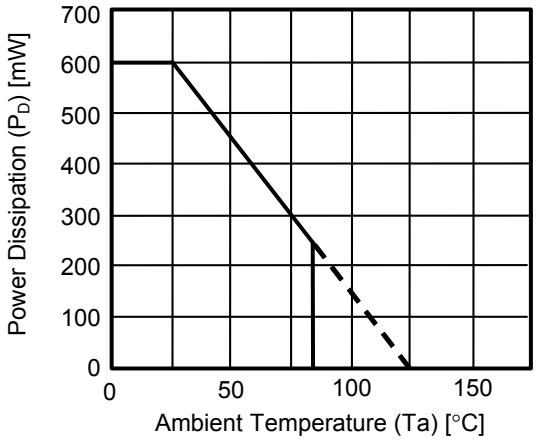


Figure 4 Power Dissipation of Package (When Mounted on Board)

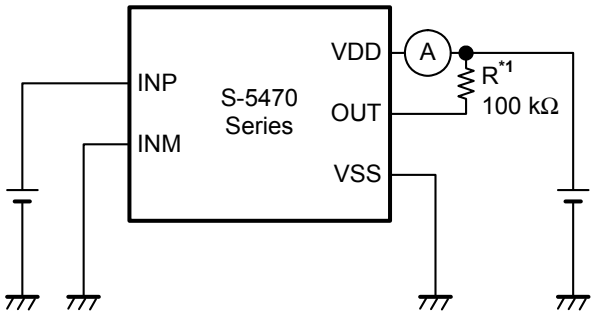
■ Electrical Characteristics

Table 5

(Ta = +25°C, V_{DD} = 3.0 V unless otherwise specified)

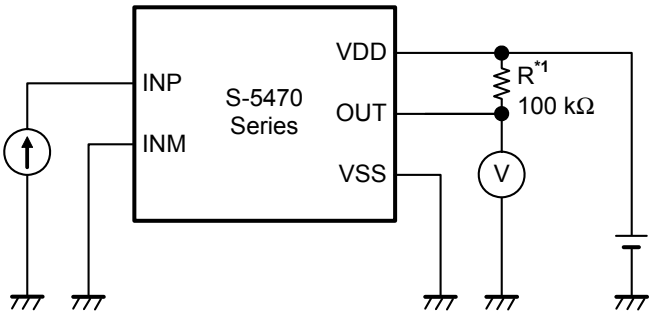
Item	Symbol	Condition		Min.	Typ.	Max.	Unit	Test Circuit
Power supply voltage	V_{DD}	Ta = –40°C to +85°C		0.9	–	5.5	V	–
Current consumption	I_{DD}	V_{INP} = V_{SS}, V_{INM} = V_{SS}		–	0.01	10	nA	1
		V_{INP} = 1.0 V, V_{INM} = V_{SS}		–	0.02	10	nA	1
Detection current	I_{DET}	–		0.52	0.7	0.88	nA	2
Release current	I_{REL}	–		I_{DET} × 0.7	I_{DET} × 0.8	I_{DET} × 0.9	nA	2
Detection current temperature coefficient	I_{tc}	Ta = –40°C to +85°C		–	±0.5	–	%/°C	–
Input current	I_{INP}	V_{INP} = 1.0 V		20	–	–	µA	3
	I_{INM}	V_{INM} = 1.0 V		10	–	–	µA	3
Current amplifier current amplification ratio × 2	G_{INM}	–		1.8	2.0	2.2	Times	4
Source current	I_{SOURCE}	CMOS output product V_{OUT} = V_{DD} – 0.3 V	V_{DD} = 0.9 V	0.01	0.4	–	mA	5
			V_{DD} = 3.0 V	3.5	4.8	–	mA	5
Sink current	I_{SINK}	V_{OUT} = 0.3 V	V_{DD} = 0.9 V	0.5	1.7	–	mA	6
			V_{DD} = 3.0 V	7.0	9.2	–	mA	6
Output response time	t_{OD}	–		–	–	15	ms	–

■ Test Circuits



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 5 Test Circuit 1



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 6 Test Circuit 2

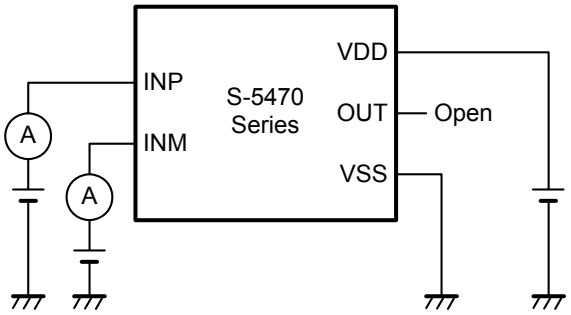
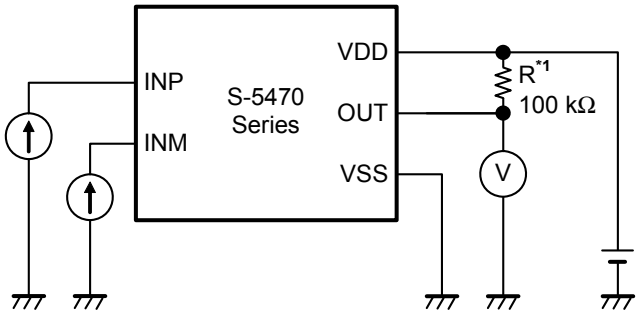


Figure 7 Test Circuit 3



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 8 Test Circuit 4

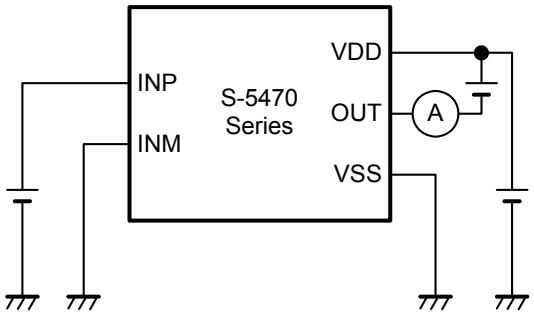


Figure 9 Test Circuit 5

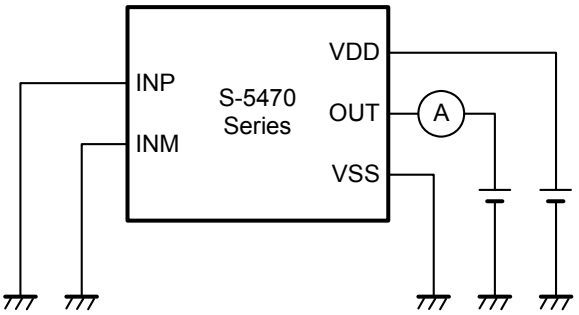
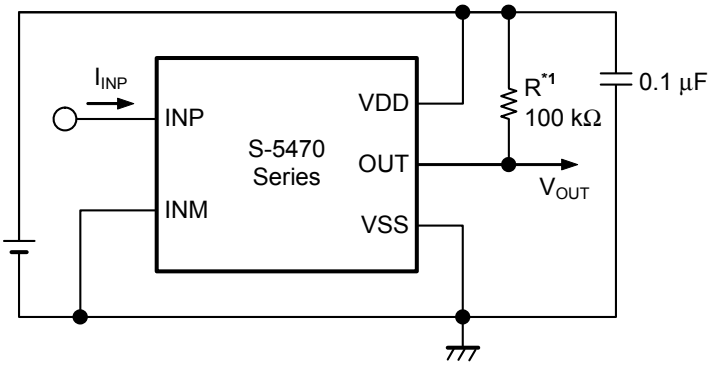


Figure 10 Test Circuit 6

■ Standard Circuits

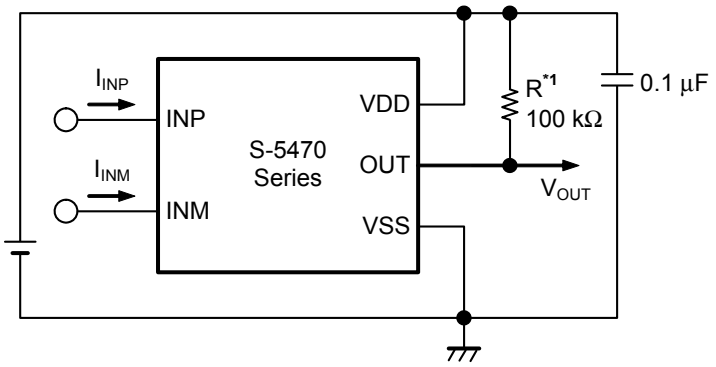
1. Certain photocurrent level detector



***1.** Resistor (R) is unnecessary for the CMOS output product.

Figure 11

2. Photocurrent level difference detector



***1.** Resistor (R) is unnecessary for the CMOS output product.

Figure 12

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

The S-5470 Series detects either certain photocurrent level or the difference of photocurrent level.
The operation of the S-5470 Series is described below, using CMOS output and active "H" products as examples.

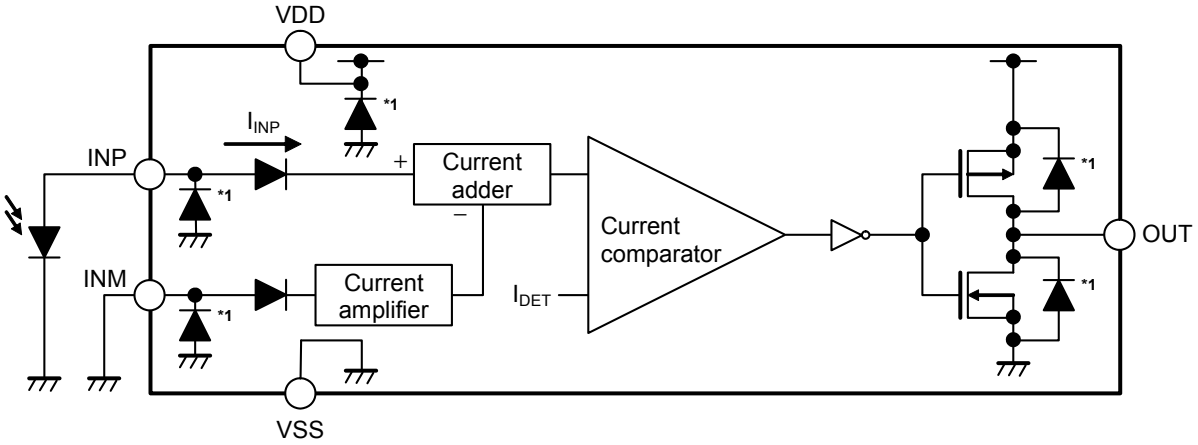
1. Basic operation when detecting certain photocurrent level (INM pin = V_{SS})

The S-5470 Series operates as follows when the INM pin is connected to VSS pin.

(1) If I_{INP} is lower than I_{DET}, an "L" level signal is output from the OUT pin.
(2) If I_{INP} increases and becomes equal to or higher than I_{DET}, an "H" level signal is output from the OUT pin (point A in **Figure 14**). Even if I_{INP} decreases and falls below I_{DET}, as long as I_{INP} is higher than I_{REL}, an "H" level signal is output from the OUT pin.
(3) If I_{INP} then decreases further and becomes equal to or lower than I_{REL}, an "L" level signal is output from the OUT pin (point B in **Figure 14**).

Remark I_{INP}: Current input to the INP pin
I_{DET}: Detection current (refer to "**4. 1 Detection current (I_{DET})**")
I_{REL}: Release current (refer to "**4. 2 Release current (I_{REL})**")

Caution 1. There are internal diodes at the INP pin and the INM pin. Therefore, in order to input a current to the INP pin and the INM pin, an input voltage of at least the forward voltage of these diodes is required.
2. Feed-through current (I_{PEAK} = 100 nA) flows around the time when the OUT pin voltage switches, as shown in Figure 14. Therefore, if the input current is fixed around this time, the current consumption will increase.



***1.** Parasitic diode

Figure 13 Diagram of the Operation when Detecting Photocurrent Level

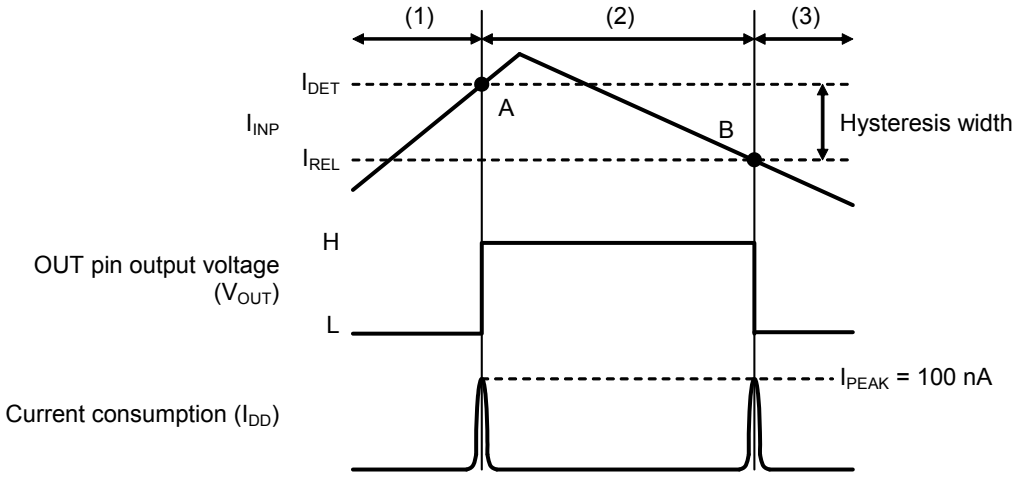


Figure 14 Operation when Detecting Certain Photocurrent Level

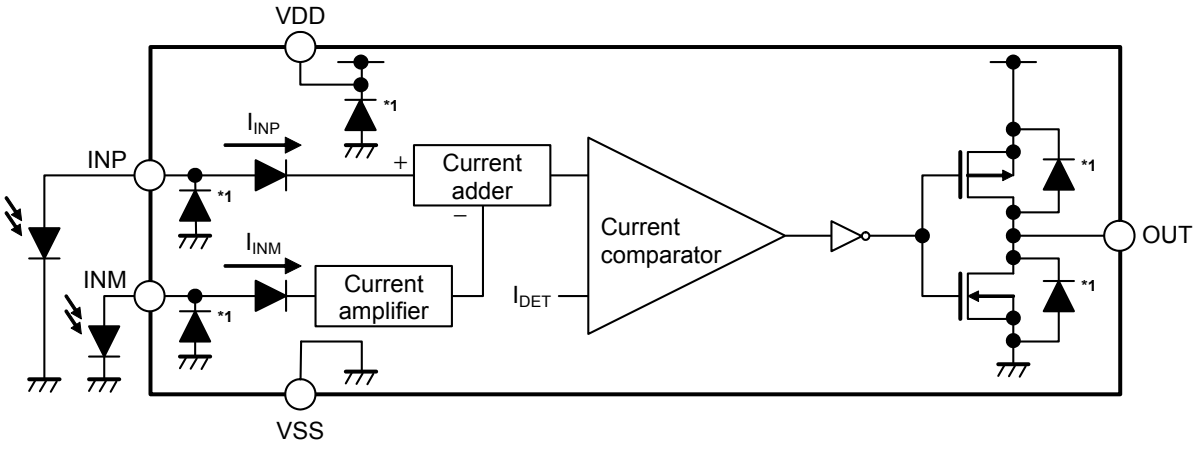
2. Basic operation when detecting the difference of photocurrent level (Current amplifier current amplification ratio × G_{INM})

The S-5470 Series operates as follows when current (I_{INM}) is applied to the INM pin.

(1) If I_{INP} is lower than $I_{DET} + G_{INM} \times I_{INM}$, an "L" level signal is output from the OUT pin.
(2) If I_{INP} increases and becomes equal to or higher than $I_{DET} + G_{INM} \times I_{INM}$, an "H" level signal is output from the OUT pin (point A in **Figure 16**). Even if I_{INP} decreases and falls below $I_{DET} + G_{INM} \times I_{INM}$, as long as I_{INP} is higher than $I_{REL} + G_{INM} \times I_{INM}$, an "H" level signal is output from the OUT pin.
(3) If I_{INP} then decreases further and becomes equal to or lower than $I_{REL} + G_{INM} \times I_{INM}$, an "L" level signal is output from the OUT pin (point B in **Figure 16**).

Remark I_{INP}: Current input to the INP pin
I_{INM}: Current input to the INM pin
I_{DET}: Detection current (refer to "**4. 1 Detection current (I_{DET})**")
I_{REL}: Release current (refer to "**4. 2 Release current (I_{REL})**")

Caution 1. There are internal diodes at the INP pin and the INM pin. Therefore, in order to input a current to the INP pin and the INM pin, an input voltage of at least the forward voltage of these diodes is required.
2. Feed-through current (I_{PEAK} = 100 nA) flows around the time when the OUT pin voltage switches, as shown in Figure 16. Therefore, if the input current is fixed around this time, the current consumption will increase.



***1.** Parasitic diode

Figure 15 Diagram of the Operation when Detecting the Difference of Photocurrent Level

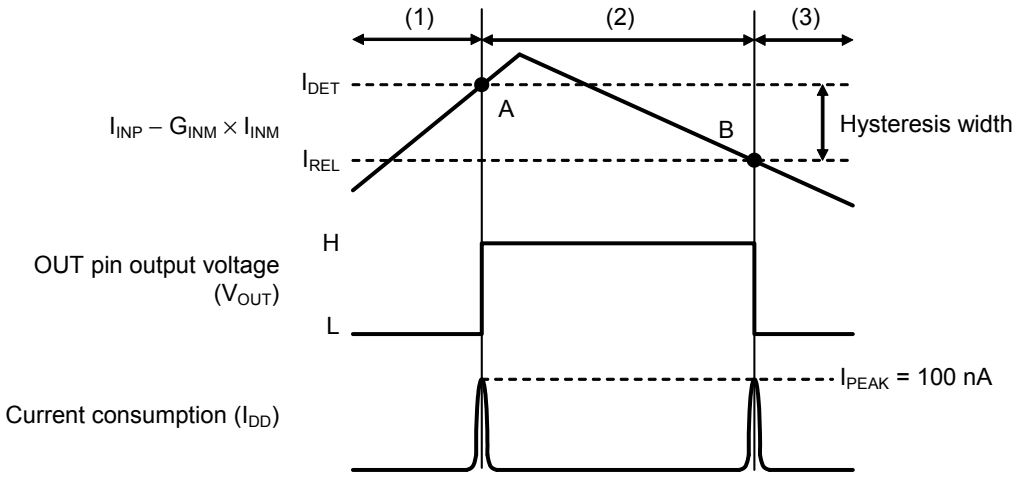
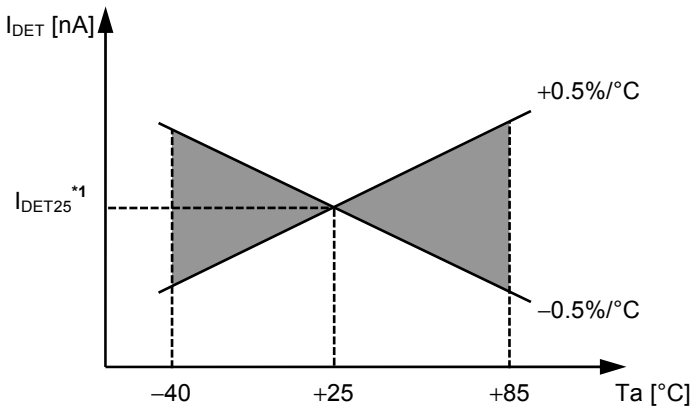


Figure 16 Operation when Detecting the Difference of Photocurrent Level

3. Temperature characteristics of detection current

The shaded area in **Figure 17** shows the temperature characteristics of the detection voltage in the operation temperature range.



***1.** I_{DET25}: Detection current value at Ta = +25°C

Figure 17 Temperature Characteristics of Detection Current

4. Explanation of terms

4. 1 Detection current (I_{DET})

The detection current (I_{DET}) is the current at which the output switches to "H".
The detection current varies slightly even among products with the same specification. The variation in detection current from the minimum detection current (I_{DET} min.) to the maximum detection current (I_{DET} max.) is called the detection current range (refer to **Figure 18**).

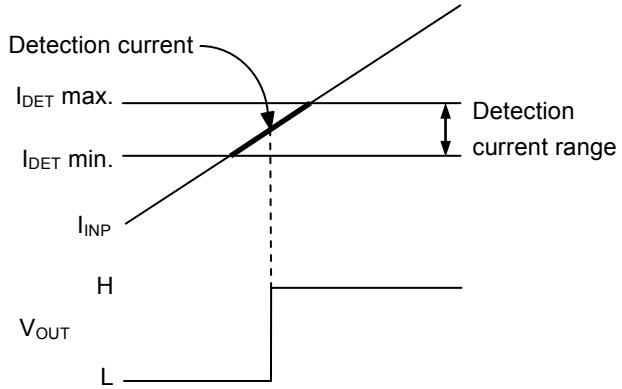


Figure 18 Detection Current

4. 2 Release current (I_{REL})

The release current (I_{REL}) is the current at which the output switches to "L".
The release current varies slightly even among products with the same specification. The variation in release current from the minimum release current (I_{REL} min.) to the maximum release current (I_{REL} max.) is called the release current range (refer to **Figure 19**).
The range is calculated from the actual detection current (I_{DET}) of a product and is in the range of $I_{DET} \times 0.7 \leq I_{REL} \leq I_{DET} \times 0.9$.

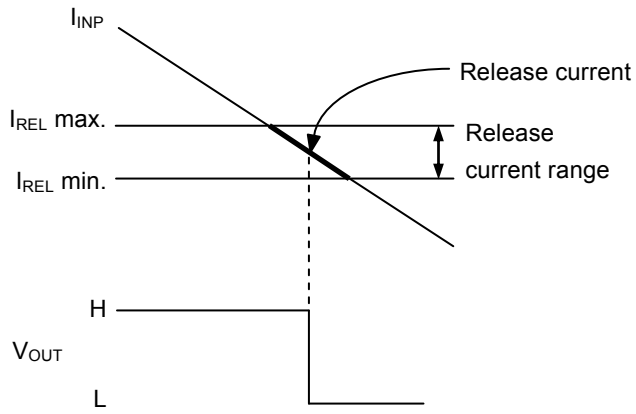


Figure 19 Release Current

4. 3 Hysteresis width

The hysteresis width is the current difference between the detection current and the release current (current at point B − current at point A in "**Figure 14 Operation when Detecting Certain Photocurrent Level**" and "**Figure 16 Operation when Detecting the Difference of Photocurrent Level**").
The hysteresis width between the detection current and the release current prevents malfunction caused by noise in the input current.

■ Application Circuits

1. Certain photocurrent level detector

If PD or LED exceeds a certain value, the output signal inverts.

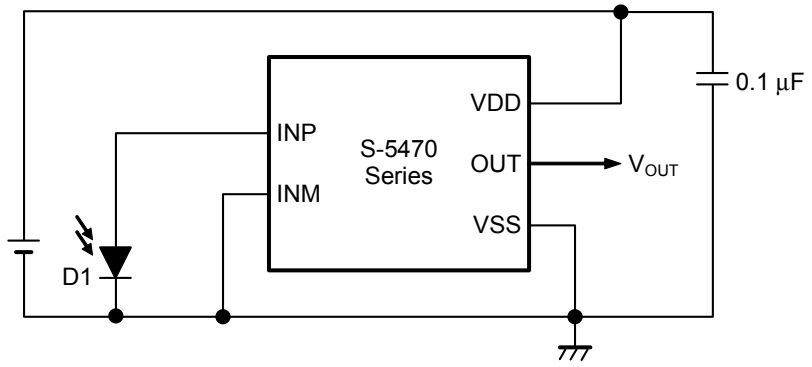


Figure 20 Example Certain Photocurrent Level Detector (CMOS Output Product)

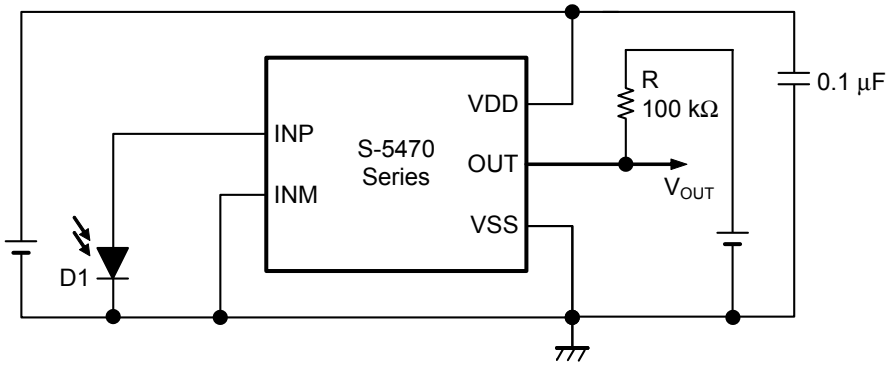


Figure 21 Example Certain Photocurrent Level Detector (Nch Open-drain Output Product)

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

2. Photocurrent level difference detector

If the difference in the photocurrent generated by the two PDs or the two LEDs exceeds a certain value, the output signal inverts.

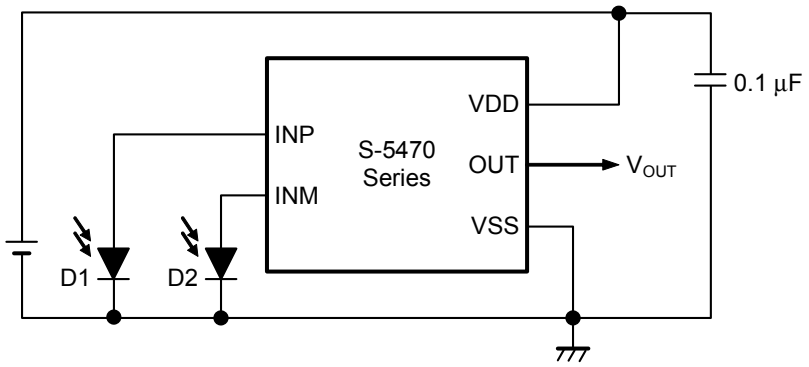


Figure 22 Example Photocurrent Level Difference Detector (CMOS Output Product)

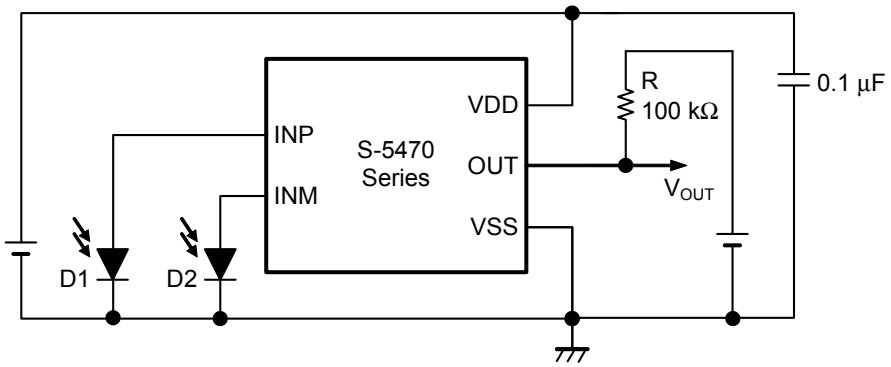


Figure 23 Example Photocurrent Level Difference Detector (Nch Open-drain Output Product)

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

3. Selection of PD or LED

Use PD or LED whose generation voltage is 1.0 V or more under usable light quantity.
Moreover, as for the test circuit shown in **Figure 24**, select PD or LED that satisfies the conditions below with detection or measurement of the quantity of light incidence in usage environment.

- Certain photocurrent level detector
  $I_{DET} \leq I$
- Photocurrent level difference detector
  $1\ nA \leq I \leq 20\ \mu A$

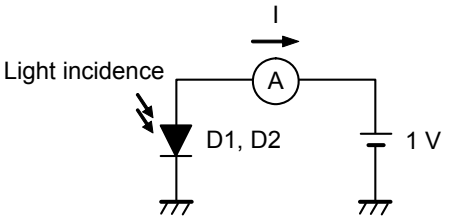


Figure 24

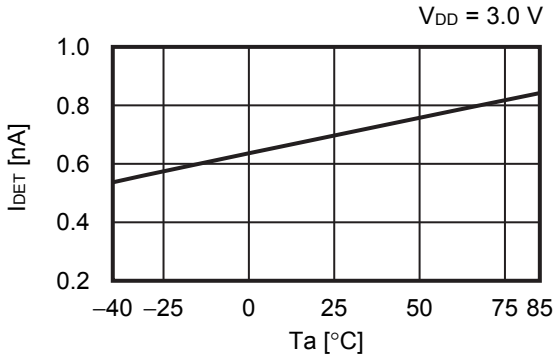
Caution 1. Select PD and LED after thorough evaluation with actual application. SII Semiconductor Corporation shall not take responsibility for operation and characteristics of PD and LED.
2. As for the circuit of detecting photocurrent difference, shown in Figure 22 and Figure 23, use the two PDs or the two LEDs that have the same characteristics in generation voltage and in generation current, respectively.

■ Precautions

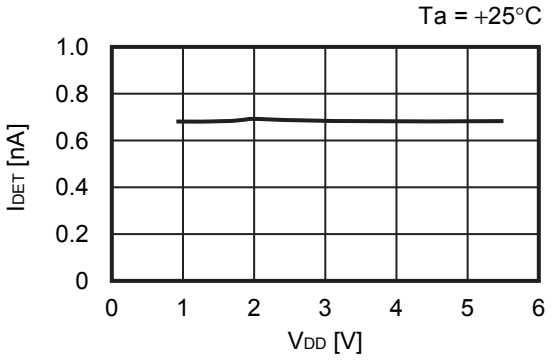
- Use the S-5470 Series with the output current of 20 mA or less.
- The S-5470 Series may malfunction if the power supply voltage changes suddenly.
- As for the detecting circuit of the photocurrent difference (Refer to "**Figure 22, Figure 23 Example Photocurrent Level Difference Detector**"), use the S-5470 Series when input current of INP pin is 20 μA or less and input current of INM pin is 10 μA or less. In case of input current excess, note that the S-5470 Series might malfunction.
- The output in the S-5470 Series is unstable in lower voltage than the minimum operation voltage. At the time of power-on, use the S-5470 Series after output stabilization.
- Set a capacitor of 0.1 μF or more between the VDD pin and VSS pin for stabilization.
- Since INP pin and INM pin is easy to be affected by disturbance noise, perform countermeasures such as mounting external parts to ICs as close as possible.
- If power impedance is high, the S-5470 Series may malfunction due to voltage drop caused by feed-through current. Set wire patterns carefully for lower power impedance.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- SII Semiconductor Corporation claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Characteristics (Typical Data)

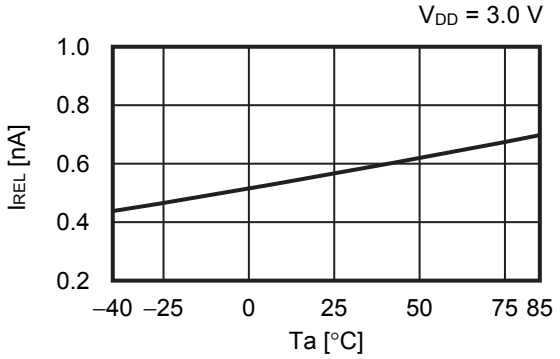
1. Detection current vs. Temperature



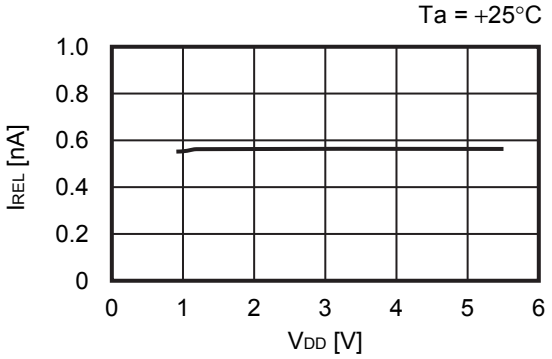
2. Detection current vs. Power supply voltage



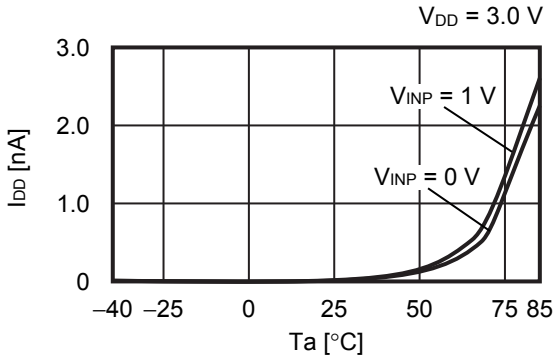
3. Release current vs. Temperature



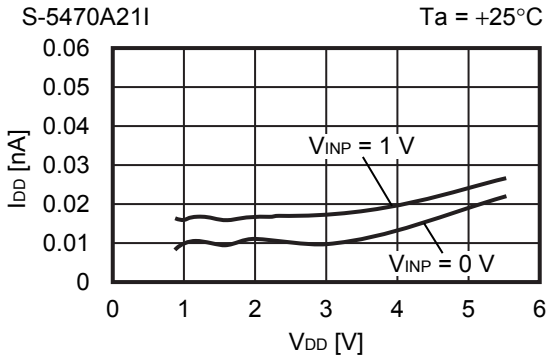
4. Release current vs. Power supply voltage

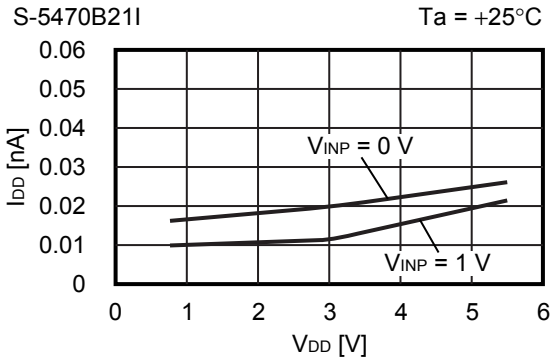


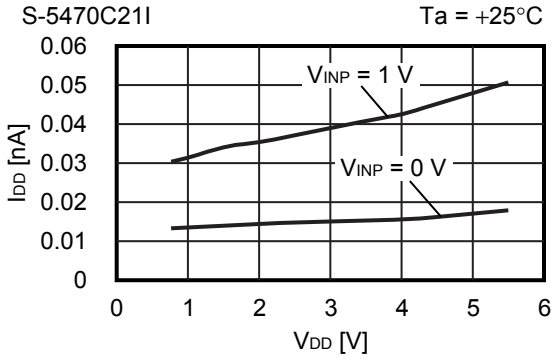
5. Current consumption vs. Temperature

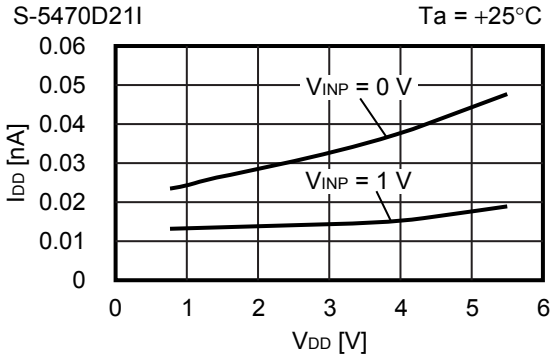


6. Current consumption vs. Power supply

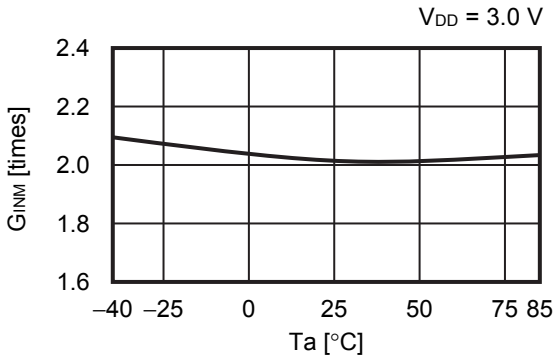




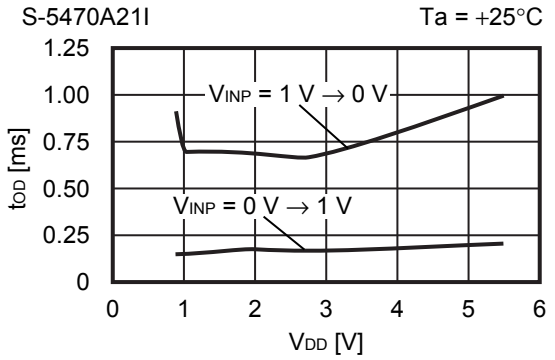


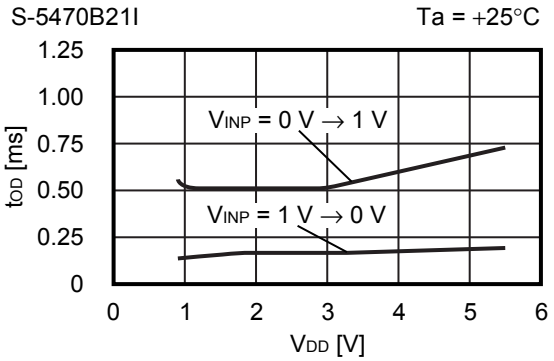


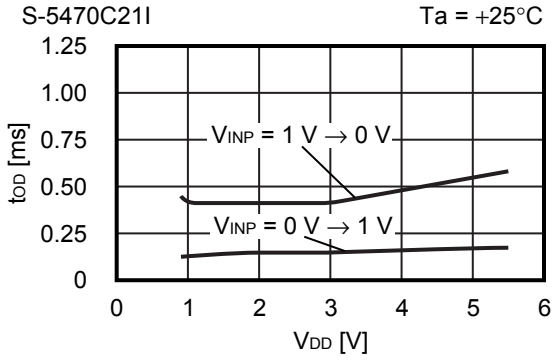
7. Current amplifier current amplication ratio vs. Temperature

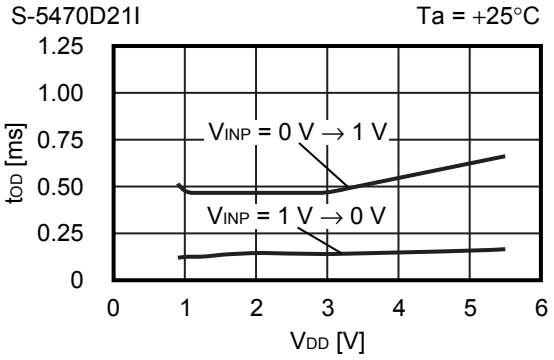


8. Output response time vs. Power supply voltage

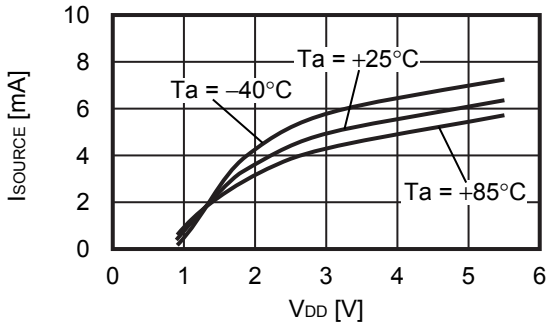




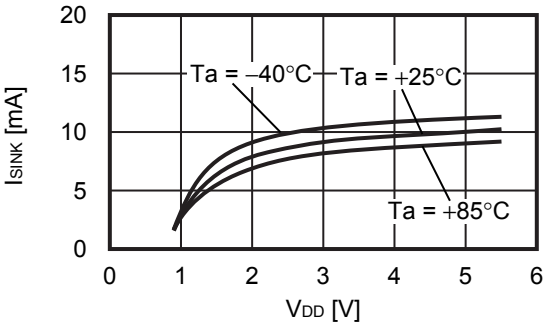




9. Source current vs. Power supply voltage



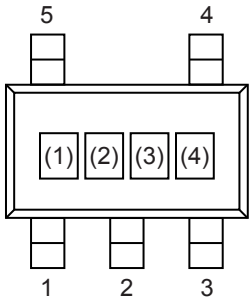
10. Sink current vs. Power supply voltage



■ Marking Specification

1. SOT-23-5

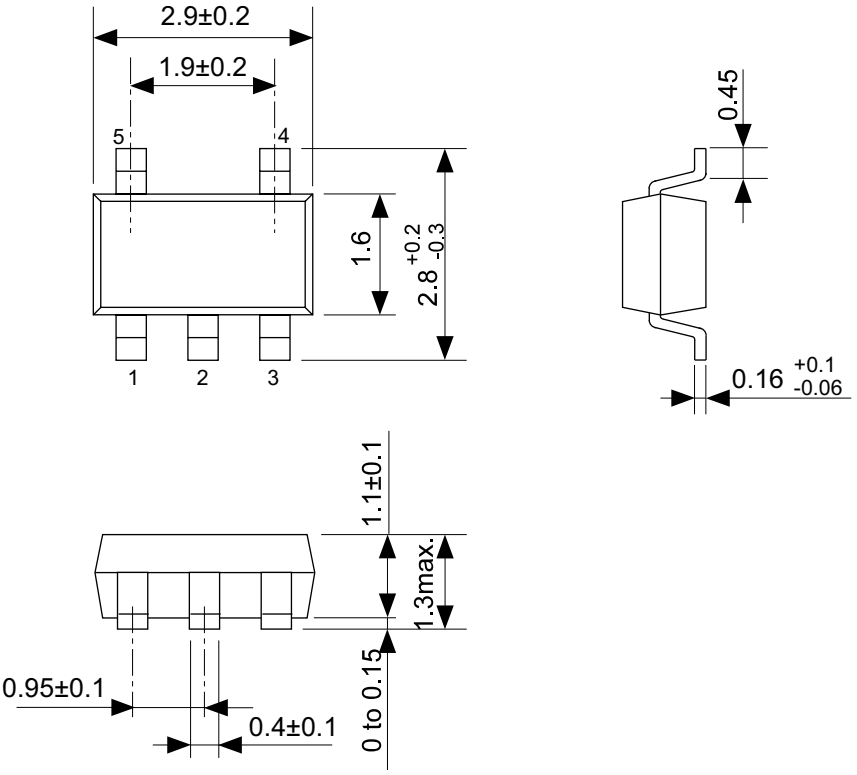
Top view



(1) to (3): Product code (Refer to **Product name vs. Product code**)
(4): Lot number

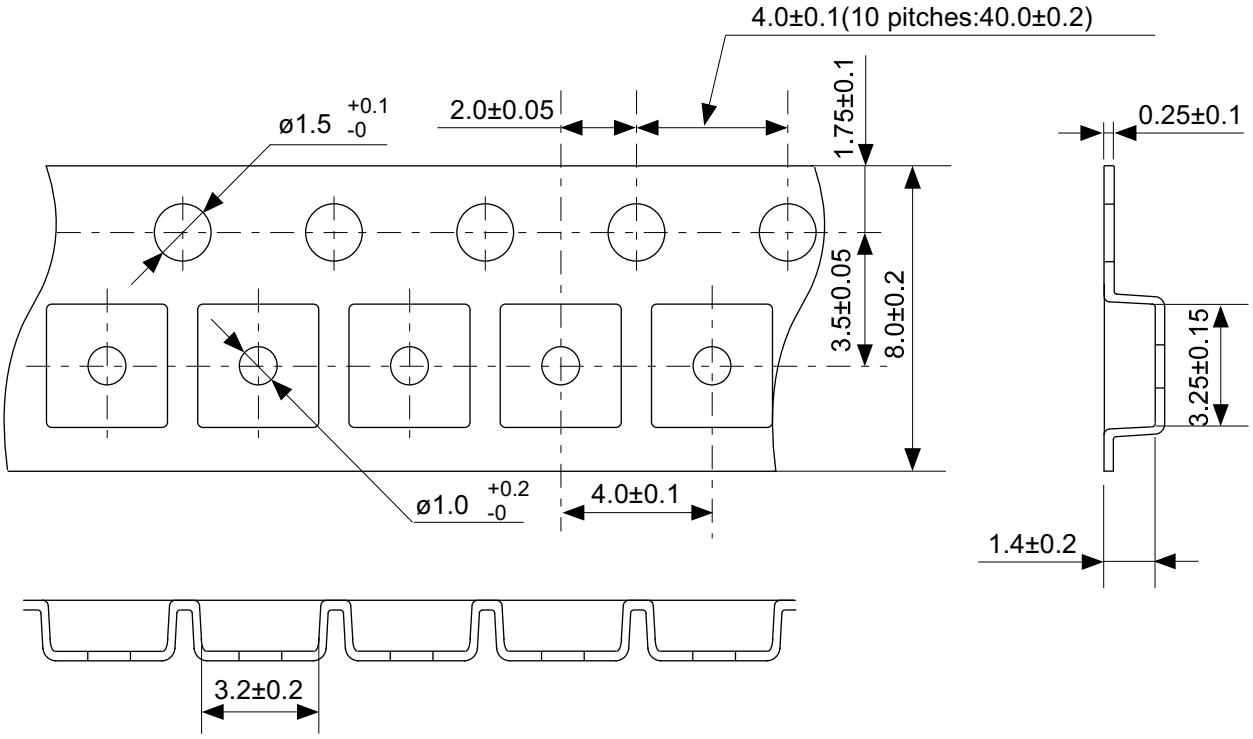
Product name vs. Product code

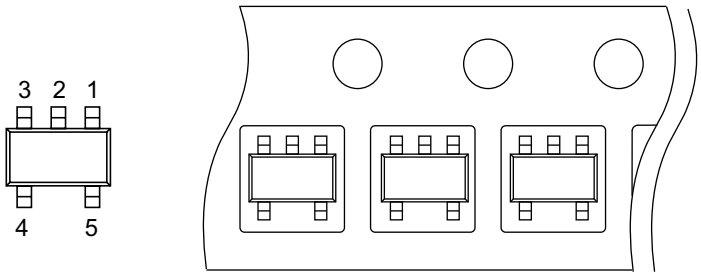
Product Name	Product Code		
	(1)	(2)	(3)
S-5470A21I-M5T1U	Y	H	A
S-5470B21I-M5T1U	Y	H	I
S-5470C21I-M5T1U	Y	H	Q
S-5470D21I-M5T1U	Y	H	Y



No. MP005-A-P-SD-1.2

TITLE	SOT235-A-PKG Dimensions
No.	MP005-A-P-SD-1.2
SCALE	
UNIT	mm
SII Semiconductor Corporation	

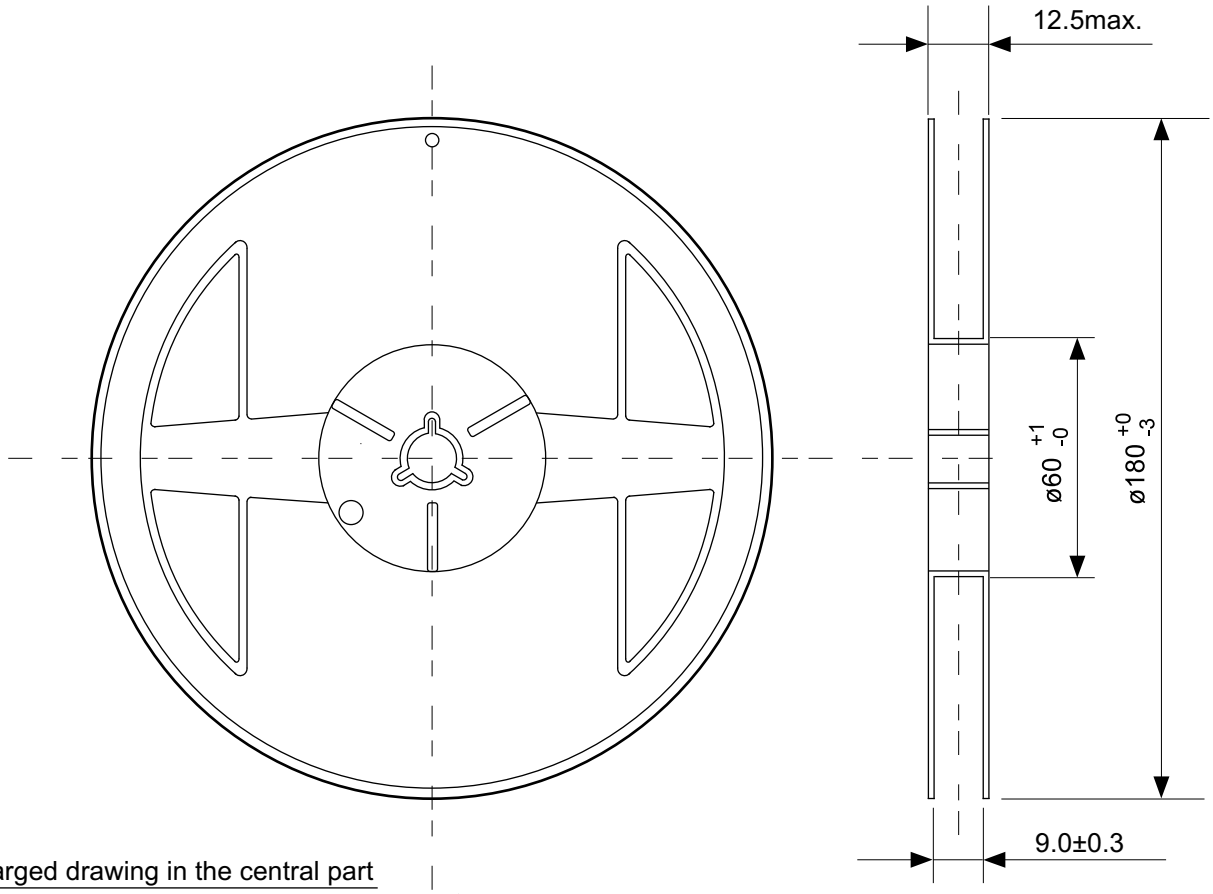




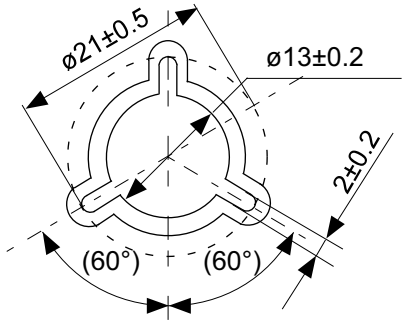
Feed direction

No. MP005-A-C-SD-2.1

TITLE	SOT235-A-Carrier Tape
No.	MP005-A-C-SD-2.1
SCALE	
UNIT	mm
SII Semiconductor Corporation	



Enlarged drawing in the central part



No. MP005-A-R-SD-1.1

TITLE	SOT235-A-Reel		
No.	MP005-A-R-SD-1.1		
SCALE		QTY.	3,000
UNIT	mm		
SII Semiconductor Corporation			

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